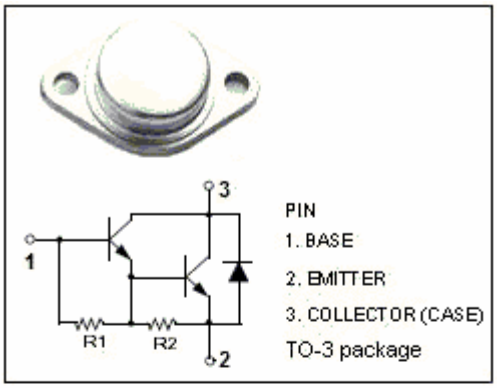
isc Silicon NPN Darlingtion Power Transistor 2SD803

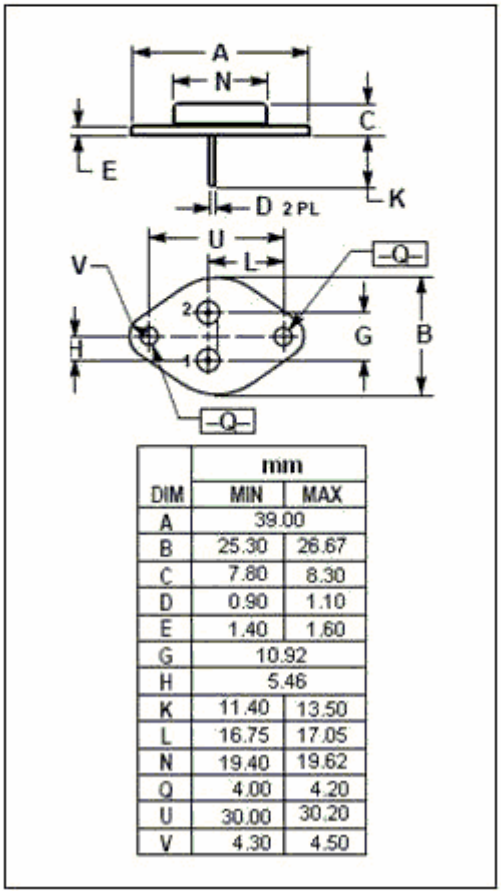
DESCRIPTION

- Built-in Base-Emitter Shunt Resistors
- High DC current gain-
  h_{FE} = 2000 (Min) @ I_C =1 Adc
- Collector-Emitter Breakdown Voltage-
  $V_{(BR)CEO}$= 100V(Min)
- Wide Area of Safe Operation



APPLICATIONS

- Designed for high power amplifier applications.



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.30
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.40	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

ABSOLUTE MAXIMUM RATINGS(T_C=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	120	V
V_{CEO}	Collector-Emitter Voltage	100	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	8	A
I_B	Base Current -Continuous	1	A
P_C	Collector Power Dissipation@T_C=25℃	100	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-65~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 50mA ; I_B= 0	100		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 3A; I_B= 30mA		1.5	V
I_{CBO}	Collector Cutoff current	V_{CB}= 120V; I_E=0		100	μA
I_{EBO}	Emitter Cut-off current	V_{EB}= 6V; I_C= 0		10	mA
h_{FE-1}	DC Current Gain	I_C= 1A ; V_{CE}= 4V	2000		
h_{FE-2}	DC Current Gain	I_C= 40A ; V_{CE}= 4V	7		